

[Claims]

[Claim 1]

A polishing composition for silicon wafer, the polishing composition comprising an abrasive, a cellulose derivative, a basic compound, and water, wherein the polishing composition has a zeta potential of -24.0 mV or more and less than 0.0 mV, wherein the cellulose derivative has a weight average molecular weight of more than 80×10^4 .

[Claim 2]

The polishing composition according to claim 1, wherein a content of the cellulose derivative is 0.1 to 20 parts by weight per 100 parts by weight of the abrasive.

[Claim 3]

The polishing composition according to claim 1 or 2, wherein a content of the basic compound is 0.001% by weight or more and less than 0.1% by weight.

[Claim 4]

The polishing composition according to any one of claims 1 to 3, wherein the polishing composition has a pH of 8.0 or more and 12.0 or less.

[Claim 5]

The polishing composition according to any one of claims 1 to 4, wherein the abrasive is silica particles.

[Claim 6]

The polishing composition according to claim 5, wherein the silica particles have an average primary particle diameter of 5 nm or more and 100 nm or less.

[Claim 7]

The polishing composition according to any one of claims 1 to 6, in use for polishing a surface made of silicon.

[Claim 8]

Use of the polishing composition according to any one of claims 1 to 7 for final polishing of a silicon wafer.

[Claim 9]

A method for polishing a silicon wafer, the method comprising a stock polishing step and a final polishing step, wherein in the final polishing step, the silicon wafer is polished using a polishing composition comprising an abrasive, a cellulose derivative, a basic compound, and water, and having a zeta potential of -24.0 mV or more and less than 0.0 mV, wherein the cellulose derivative has a weight average molecular weight of more than 80×10^4 .